E. Lattice Semiconductor Corporation - LFE3-17EA-7LFTN256I Datasheet



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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	716800
Number of I/O	133
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	256-BGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-17ea-7lftn256i

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Figure 2-8. Clock Divider Connections



Clock Distribution Network

LatticeECP3 devices have eight quadrant-based primary clocks and eight secondary clock/control sources. Two high performance edge clocks are available on the top, left, and right edges of the device to support high speed interfaces. These clock sources are selected from external I/Os, the sysCLOCK PLLs, DLLs or routing. These clock sources are fed throughout the chip via a clock distribution system.

Primary Clock Sources

LatticeECP3 devices derive clocks from six primary source types: PLL outputs, DLL outputs, CLKDIV outputs, dedicated clock inputs, routing and SERDES Quads. LatticeECP3 devices have two to ten sysCLOCK PLLs and two DLLs, located on the left and right sides of the device. There are six dedicated clock inputs: two on the top side, two on the left side and two on the right side of the device. Figures 2-9, 2-10 and 2-11 show the primary clock sources for LatticeECP3 devices.

Figure 2-9. Primary Clock Sources for LatticeECP3-17



Note: Clock inputs can be configured in differential or single-ended mode.



Primary Clock Routing

The purpose of the primary clock routing is to distribute primary clock sources to the destination quadrants of the device. A global primary clock is a primary clock that is distributed to all quadrants. The clock routing structure in LatticeECP3 devices consists of a network of eight primary clock lines (CLK0 through CLK7) per quadrant. The primary clocks of each quadrant are generated from muxes located in the center of the device. All the clock sources are connected to these muxes. Figure 2-12 shows the clock routing for one quadrant. Each quadrant mux is identical. If desired, any clock can be routed globally.

Figure 2-12. Per Quadrant Primary Clock Selection



Dynamic Clock Control (DCC)

The DCC (Quadrant Clock Enable/Disable) feature allows internal logic control of the quadrant primary clock network. When a clock network is disabled, all the logic fed by that clock does not toggle, reducing the overall power consumption of the device.

Dynamic Clock Select (DCS)

The DCS is a smart multiplexer function available in the primary clock routing. It switches between two independent input clock sources without any glitches or runt pulses. This is achieved regardless of when the select signal is toggled. There are two DCS blocks per quadrant; in total, there are eight DCS blocks per device. The inputs to the DCS block come from the center muxes. The output of the DCS is connected to primary clocks CLK6 and CLK7 (see Figure 2-12).

Figure 2-13 shows the timing waveforms of the default DCS operating mode. The DCS block can be programmed to other modes. For more information about the DCS, please see the list of technical documentation at the end of this data sheet.



Figure 2-13. DCS Waveforms



as, overflow, underflow and convergent rounding, etc.

- Flexible cascading across slices to get larger functions
- RTL Synthesis friendly synchronous reset on all registers, while still supporting asynchronous reset for legacy users
- Dynamic MUX selection to allow Time Division Multiplexing (TDM) of resources for applications that require processor-like flexibility that enables different functions for each clock cycle

For most cases, as shown in Figure 2-24, the LatticeECP3 DSP slice is backwards-compatible with the LatticeECP2[™] sysDSP block, such that, legacy applications can be targeted to the LatticeECP3 sysDSP slice. The functionality of one LatticeECP2 sysDSP Block can be mapped into two adjacent LatticeECP3 sysDSP slices, as shown in Figure 2-25.



Figure 2-24. Simplified sysDSP Slice Block Diagram



Figure 2-25. Detailed sysDSP Slice Diagram



Note: A_ALU, B_ALU and C_ALU are internal signals generated by combining bits from AA, AB, BA BB and C inputs. See TN1182, LatticeECP3 sysDSP Usage Guide, for further information.

The LatticeECP2 sysDSP block supports the following basic elements.

- MULT (Multiply)
- MAC (Multiply, Accumulate)
- MULTADDSUB (Multiply, Addition/Subtraction)
- MULTADDSUBSUM (Multiply, Addition/Subtraction, Summation)

Table 2-8 shows the capabilities of each of the LatticeECP3 slices versus the above functions.

 Table 2-8. Maximum Number of Elements in a Slice

Width of Multiply	x9	x18	x36
MULT	4	2	1/2
MAC	1	1	—
MULTADDSUB	2	1	—
MULTADDSUBSUM	1 ¹	1/2	_

1. One slice can implement 1/2 9x9 m9x9addsubsum and two m9x9addsubsum with two slices.

Some options are available in the four elements. The input register in all the elements can be directly loaded or can be loaded as a shift register from previous operand registers. By selecting "dynamic operation" the following operations are possible:

- In the Add/Sub option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.



SCI (SERDES Client Interface) Bus

The SERDES Client Interface (SCI) is an IP interface that allows the SERDES/PCS Quad block to be controlled by registers rather than the configuration memory cells. It is a simple register configuration interface that allows SERDES/PCS configuration without power cycling the device.

The Diamond and ispLEVER design tools support all modes of the PCS. Most modes are dedicated to applications associated with a specific industry standard data protocol. Other more general purpose modes allow users to define their own operation. With these tools, the user can define the mode for each quad in a design.

Popular standards such as 10Gb Ethernet, x4 PCI Express and 4x Serial RapidIO can be implemented using IP (available through Lattice), a single quad (Four SERDES channels and PCS) and some additional logic from the core.

The LatticeECP3 family also supports a wide range of primary and secondary protocols. Within the same quad, the LatticeECP3 family can support mixed protocols with semi-independent clocking as long as the required clock frequencies are integer x1, x2, or x11 multiples of each other. Table 2-15 lists the allowable combination of primary and secondary protocol combinations.

Flexible Quad SERDES Architecture

The LatticeECP3 family SERDES architecture is a quad-based architecture. For most SERDES settings and standards, the whole quad (consisting of four SERDES) is treated as a unit. This helps in silicon area savings, better utilization and overall lower cost.

However, for some specific standards, the LatticeECP3 quad architecture provides flexibility; more than one standard can be supported within the same quad.

Table 2-15 shows the standards can be mixed and matched within the same quad. In general, the SERDES standards whose nominal data rates are either the same or a defined subset of each other, can be supported within the same quad. In Table 2-15, the Primary Protocol column refers to the standard that determines the reference clock and PLL settings. The Secondary Protocol column shows the other standard that can be supported within the same quad.

Furthermore, Table 2-15 also implies that more than two standards in the same quad can be supported, as long as they conform to the data rate and reference clock requirements. For example, a quad may contain PCI Express 1.1, SGMII, Serial RapidIO Type I and Serial RapidIO Type II, all in the same quad.

Table 2-15. LatticeECP3 Primary and Secondary Protocol Support

Primary Protocol	Secondary Protocol
PCI Express 1.1	SGMII
PCI Express 1.1	Gigabit Ethernet
PCI Express 1.1	Serial RapidIO Type I
PCI Express 1.1	Serial RapidIO Type II
Serial RapidIO Type I	SGMII
Serial RapidIO Type I	Gigabit Ethernet
Serial RapidIO Type II	SGMII
Serial RapidIO Type II	Gigabit Ethernet
Serial RapidIO Type II	Serial RapidIO Type I
CPRI-3	CPRI-2 and CPRI-1
3G-SDI	HD-SDI and SD-SDI



MCCLK (MHz)	MCCLK (MHz)
	10
2.5 ¹	13
4.3	15 ²
5.4	20
6.9	26
8.1	33 ³
9.2	

 Table 2-16. Selectable Master Clock (MCCLK) Frequencies During Configuration (Nominal)

1. Software default MCCLK frequency. Hardware default is 3.1 MHz.

2. Maximum MCCLK with encryption enabled.

3. Maximum MCCLK without encryption.

Density Shifting

The LatticeECP3 family is designed to ensure that different density devices in the same family and in the same package have the same pinout. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likelihood of success in each case. An example is that some user I/Os may become No Connects in smaller devices in the same package. Refer to the LatticeECP3 Pin Migration Tables and Diamond software for specific restrictions and limitations.



LatticeECP3 Family Data Sheet DC and Switching Characteristics

April 2014

Data Sheet DS1021

Absolute Maximum Ratings^{1, 2, 3}

Supply Voltage V_CC
Supply Voltage V_{CCAUX} $\ldots \ldots \ldots \ldots -0.5$ V to 3.75 V
Supply Voltage V_{CCJ}
Output Supply Voltage V_{CCIO} –0.5 V to 3.75 V
Input or I/O Tristate Voltage Applied $^4.$ –0.5 V to 3.75 V
Storage Temperature (Ambient)
Junction Temperature (T_J) +125 °C

^{1.} Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

3. All voltages referenced to GND.

4. Overshoot and undershoot of -2 V to (V_{IHMAX} + 2) volts is permitted for a duration of <20 ns.

Recommended Operating Conditions¹

Symbol	Parameter	Min.	Max.	Units
V _{CC} ²	Core Supply Voltage	1.14	1.26	V
V _{CCAUX} ^{2, 4}	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V _{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V _{CCIO} ^{2, 3}	I/O Driver Supply Voltage	1.14	3.465	V
V _{CCJ} ²	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V _{TT} ⁵	Termination Voltage	0.5	1.3125	V
t _{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t _{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Pow	er Supply ⁶			
V	Input Buffer Power Supply (1.2 V)	1.14	1.26	V
V CCIB	Input Buffer Power Supply (1.5 V)	1.425	1.575	V
V	Output Buffer Power Supply (1.2 V)		1.26	V
VCCOB	Output Buffer Power Supply (1.5 V)	1.425	1.575	V
V _{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.

If V_{CCIO} or V_{CCJ} is set to 1.2 V, they must be connected to the same power supply as V_{CC.} If V_{CCIO} or V_{CCJ} is set to 3.3 V, they must be connected to the same power supply as V_{CCAUX}.

3. See recommended voltages by I/O standard in subsequent table.

4. V_{CCAUX} ramp rate must not exceed 30 mV/µs during power-up when transitioning between 0 V and 3.3 V.

5. If not used, V_{TT} should be left floating.

6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

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sysl/O Single-Ended DC Electrical Characteristics

Input/Output	V _{IL}		V _{IH}		Voi	Vou			
Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)	l _{OL} ¹ (mA)	I _{OH} ¹ (mA)	
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V _{CCIO} - 0.2	0.1	-0.1	
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V _{CCIO} - 0.2	0.1	-0.1	
LVCMOS18	-0.3	0.35 V _{CCIO}	0.65 V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	16, 12, 8, 4	-16, -12, -8, -4	
					0.2	V _{CCIO} - 0.2	0.1	-0.1	
	-03	0.35 Vacua	0.65 Vacia	36	0.4	V _{CCIO} - 0.4	8, 4	-8, -4	
	-0.5	0.00 VCCIO	0.03 VCCIO	5.0	0.2	V _{CCIO} - 0.2	0.1	-0.1	
	-0.3	0.35 Vaa	0.65 Vaa	3.6	0.4	V _{CCIO} - 0.4	6, 2	-6, -2	
20000012	-0.0	0.00 VCC	0.03 VCC	0.0	0.2	V _{CCIO} - 0.2	0.1	-0.1	
LVTTL33	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V _{CCIO} - 0.2	0.1	-0.1	
PCI33	-0.3	0.3 V _{CCIO}	0.5 V _{CCIO}	3.6	0.1 V _{CCIO}	0.9 V _{CCIO}	1.5	-0.5	
SSTL18_I	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	3.6	0.4	V _{CCIO} - 0.4	6.7	-6.7	
SSTL18_II	_0.3	V0 125	V + 0.125	3.6	0.28	V 0 28	8	-8	
(DDR2 Memory)	-0.3	V _{REF} - 0.123	V _{REF} + 0.125	3.0	0.0	0.20	V CCIO - 0.20	11	-11
SSTI 2 1	_0.3	V0 18	V \ 0.18	3.6	0.54	V	7.6	-7.6	
551L2_1	-0.5	V _{REF} - 0.10	V _{REF} + 0.10	5.0	0.54	V CCIO - 0.02	12	-12	
SSTL2_II	_0.3	V0.18	V \ 0.18	3.6	0.35	V	15.2	-15.2	
(DDR Memory)	-0.5	V _{REF} - 0.10	V _{REF} + 0.10	5.0	0.00	V CCIO - 0.43	20	-20	
SSTL3_I	-0.3	V _{REF} - 0.2	V _{REF} + 0.2	3.6	0.7	V _{CCIO} - 1.1	8	-8	
SSTL3_II	-0.3	V _{REF} - 0.2	V _{REF} + 0.2	3.6	0.5	V _{CCIO} - 0.9	16	-16	
SSTL15	0.2	V 01	V + 0.1	2.6	0.2	V _{CCIO} - 0.3	7.5	-7.5	
(DDR3 Memory)	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	3.0	0.5	V _{CCIO} * 0.8	9	-9	
	_0.3	V01	V 101	3.6	0.4	V 0 4	4	-4	
	-0.3	V _{REF} - 0.1	VREF + 0.1	5.0	0.4	V CCIO - 0.4	8	-8	
	_0.3	V01	V + 0 1	3.6	0.4	V04	8	-8	
	-0.3	VREF - 0.1	VREF + 0.1	3.0	0.4	VCCIO - 0.4	12	-12	
HSTL18_II	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	3.6	0.4	V _{CCIO} - 0.4	16	-16	

1. For electromigration, the average DC current drawn by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed n * 8 mA, where n is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.



LVDS25E

The top and bottom sides of LatticeECP3 devices support LVDS outputs via emulated complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The scheme shown in Figure 3-1 is one possible solution for point-to-point signals.





Table 3-1. LVDS25E DC Conditions

Parameter	Description	Typical	Units
V _{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z _{OUT}	Driver Impedance	20	Ω
R _S	Driver Series Resistor (+/-1%)	158	Ω
R _P	Driver Parallel Resistor (+/-1%)	140	Ω
R _T	Receiver Termination (+/-1%)	100	Ω
V _{OH}	Output High Voltage	1.43	V
V _{OL}	Output Low Voltage	1.07	V
V _{OD}	Output Differential Voltage	0.35	V
V _{CM}	Output Common Mode Voltage	1.25	V
Z _{BACK}	Back Impedance	100.5	Ω
I _{DC}	DC Output Current	6.03	mA

LVCMOS33D

All I/O banks support emulated differential I/O using the LVCMOS33D I/O type. This option, along with the external resistor network, provides the system designer the flexibility to place differential outputs on an I/O bank with 3.3 V V_{CCIO}. The default drive current for LVCMOS33D output is 12 mA with the option to change the device strength to 4 mA, 8 mA, 16 mA or 20 mA. Follow the LVCMOS33 specifications for the DC characteristics of the LVCMOS33D.



LatticeECP3 External Switching Characteristics ^{1, 2, 3, 13}

			-	-8		-8 -7		7	-6			
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units			
Clocks				1			1		1			
Primary Clock ⁶												
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-150EA	—	500	—	420	—	375	MHz			
t _{w_PRI}	Clock Pulse Width for Primary Clock	ECP3-150EA	0.8	—	0.9		1.0		ns			
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-150EA	_	300	_	330	—	360	ps			
tskew_prib	Primary Clock Skew Within a Bank	ECP3-150EA	—	250	_	280	—	300	ps			
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-70EA/95EA	—	500	_	420	—	375	MHz			
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-70EA/95EA	0.8	—	0.9		1.0		ns			
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-70EA/95EA	—	360	_	370	—	380	ps			
t _{SKEW_PRIB}	Primary Clock Skew Within a Bank	ECP3-70EA/95EA	—	310		320	—	330	ps			
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-35EA	—	500	_	420	—	375	MHz			
tw_pri	Pulse Width for Primary Clock	ECP3-35EA	0.8	_	0.9		1.0	_	ns			
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-35EA	_	300	_	330	—	360	ps			
tskew_prib	Primary Clock Skew Within a Bank	ECP3-35EA	—	250	_	280	—	300	ps			
f _{MAX_PRI}	Frequency for Primary Clock Tree	ECP3-17EA	—	500	_	420		375	MHz			
t _{W_PRI}	Pulse Width for Primary Clock	ECP3-17EA	0.8	—	0.9	_	1.0		ns			
t _{SKEW_PRI}	Primary Clock Skew Within a Device	ECP3-17EA	_	310		340	_	370	ps			
tskew_prib	Primary Clock Skew Within a Bank	ECP3-17EA	—	220	_	230	—	240	ps			
Edge Clock ⁶												
fMAX_EDGE	Frequency for Edge Clock	ECP3-150EA	—	500	—	420	_	375	MHz			
tw_edge	Clock Pulse Width for Edge Clock	ECP3-150EA	0.9	—	1.0	—	1.2	_	ns			
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-150EA	_	200	_	210	—	220	ps			
fMAX_EDGE	Frequency for Edge Clock	ECP3-70EA/95EA	—	500	_	420	—	375	MHz			
tw_edge	Clock Pulse Width for Edge Clock	ECP3-70EA/95EA	0.9	—	1.0	_	1.2	-	ns			
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-70EA/95EA	_	200	_	210	—	220	ps			
fMAX_EDGE	Frequency for Edge Clock	ECP3-35EA	—	500	_	420	—	375	MHz			
tw_edge	Clock Pulse Width for Edge Clock	ECP3-35EA	0.9	—	1.0	—	1.2	_	ns			
tskew_edge_dqs	Edge Clock Skew Within an Edge of the Device	ECP3-35EA	_	200	_	210	—	220	ps			
fMAX_EDGE	Frequency for Edge Clock	ECP3-17EA	—	500	_	420	—	375	MHz			
tw_edge	Clock Pulse Width for Edge Clock	ECP3-17EA	0.9	—	1.0	_	1.2	_	ns			
t _{SKEW_EDGE_DQS}	Edge Clock Skew Within an Edge of the Device	ECP3-17EA	—	200	_	210	—	220	ps			
Generic SDR												
General I/O Pin Par	ameters Using Dedicated Clock In	put Primary Clock W	Vithout Pl	LL ²								
t _{co}	Clock to Output - PIO Output Register	ECP3-150EA	_	3.9	_	4.3	—	4.7	ns			
t _{SU}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.0	_	0.0		0.0		ns			
t _H	Clock to Data Hold - PIO Input Register	ECP3-150EA	1.5	—	1.7	_	2.0	_	ns			
	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.3	—	1.5	_	1.7	_	ns			

Over Recommended Commercial Operating Conditions



LatticeECP3 External Switching Characteristics (Continued)^{1, 2, 3, 13}

			-8		-7		7 –6		
Parameter	Description	Device	Min.	Max.	Min.	Max.	Min.	Max.	Units
Generic DDRX2 Ou	tput with Clock and Data (>10 Bits	Wide) Centered at Pir	n Using I	PLL (GDI	DRX2_TX	.PLL.Cer	ntered) ¹⁰		
Left and Right Side	es								
t _{DVBGDDR}	Data Valid Before CLK	All ECP3EA Devices	285	—	370	_	431	—	ps
t _{DVAGDDR}	Data Valid After CLK	All ECP3EA Devices	285	—	370	_	432	_	ps
f _{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	_	500	—	420	—	375	MHz
Memory Interface		•							
DDR/DDR2 I/O Pin	Parameters (Input Data are Strobe	Edge Aligned, Output	ut Strobe	e Edge is	Data Ce	ntered)4			
t _{DVADQ}	Data Valid After DQS (DDR Read)	All ECP3 Devices	—	0.225		0.225		0.225	UI
t _{DVEDQ}	Data Hold After DQS (DDR Read)	All ECP3 Devices	0.64	—	0.64	—	0.64	—	UI
t _{DQVBS}	Data Valid Before DQS	All ECP3 Devices	0.25	—	0.25	_	0.25	_	UI
t _{DQVAS}	Data Valid After DQS	All ECP3 Devices	0.25	—	0.25	_	0.25	_	UI
f _{MAX_DDR}	DDR Clock Frequency	All ECP3 Devices	95	200	95	200	95	166	MHz
f _{MAX_DDR2}	DDR2 clock frequency	All ECP3 Devices	125	266	125	200	125	166	MHz
DDR3 (Using PLL f	or SCLK) I/O Pin Parameters	•							
t _{DVADQ}	Data Valid After DQS (DDR Read)	All ECP3 Devices	_	0.225		0.225		0.225	UI
t _{DVEDQ}	Data Hold After DQS (DDR Read)	All ECP3 Devices	0.64	—	0.64	_	0.64	—	UI
t _{DQVBS}	Data Valid Before DQS	All ECP3 Devices	0.25	—	0.25	_	0.25	—	UI
t _{DQVAS}	Data Valid After DQS	All ECP3 Devices	0.25	—	0.25	_	0.25	—	UI
f _{MAX_DDR3}	DDR3 clock frequency	All ECP3 Devices	300	400	266	333	266	300	MHz
DDR3 Clock Timing	9								
t _{CH} (avg) ⁹	Average High Pulse Width	All ECP3 Devices	0.47	0.53	0.47	0.53	0.47	0.53	UI
t _{CL} (avg) ⁹	Average Low Pulse Width	All ECP3 Devices	0.47	0.53	0.47	0.53	0.47	0.53	UI
t _{JIT} (per, lck) ⁹	Output Clock Period Jitter During DLL Locking Period	All ECP3 Devices	-90	90	-90	90	-90	90	ps
t _{JIT} (cc, lck) ⁹	Output Cycle-to-Cycle Period Jit- ter During DLL Locking Period	All ECP3 Devices	_	180	—	180	—	180	ps

1. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

2. General I/O timing numbers based on LVCMOS 2.5, 12mA, Fast Slew Rate, 0pf load.

3. Generic DDR timing numbers based on LVDS I/O.

4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18.

5. DDR3 timing numbers based on SSTL15.

6. Uses LVDS I/O standard.

7. The current version of software does not support per bank skew numbers; this will be supported in a future release.

8. Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.

9. Using settings generated by IPexpress.

10. These numbers are generated using best case PLL located in the center of the device.

11. Uses SSTL25 Class II Differential I/O Standard.

12. All numbers are generated with ispLEVER 8.1 software.

13. For details on -9 speed grade devices, please contact your Lattice Sales Representative.



LatticeECP3 Internal Switching Characteristics^{1, 2, 5} (Continued)

		_	8	-7		-6		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units.
t _{HWREN_EBR}	Hold Write/Read Enable to EBR Memory	0.141		0.145		0.149		ns
t _{SUCE_EBR}	Clock Enable Setup Time to EBR Output Register	0.087		0.096		0.104		ns
t _{HCE_EBR}	Clock Enable Hold Time to EBR Output Register	-0.066		-0.080		-0.094		ns
t _{SUBE_EBR}	Byte Enable Set-Up Time to EBR Output Register	-0.071		-0.070		-0.068		ns
t _{HBE_EBR}	Byte Enable Hold Time to EBR Output Register	0.118	_	0.098	_	0.077	_	ns
DSP Block Tin	ning ³							
t _{SUI_DSP}	Input Register Setup Time	0.32	_	0.36	_	0.39	_	ns
t _{HI_DSP}	Input Register Hold Time	-0.17	_	-0.19	_	-0.21	_	ns
t _{SUP_DSP}	Pipeline Register Setup Time	2.23	_	2.30	_	2.37	_	ns
t _{HP_DSP}	Pipeline Register Hold Time	-1.02	_	-1.09	_	-1.15	_	ns
t _{SUO_DSP}	Output Register Setup Time	3.09	_	3.22	_	3.34	_	ns
t _{HO_DSP}	Output Register Hold Time	-1.67	_	-1.76	_	-1.84	_	ns
t _{COI_DSP}	Input Register Clock to Output Time	_	3.05	_	3.35	_	3.73	ns
t _{COP_DSP}	Pipeline Register Clock to Output Time	_	1.30	_	1.47	_	1.64	ns
t _{COO_DSP}	Output Register Clock to Output Time	—	0.58	—	0.60	—	0.62	ns
t _{SUOPT_DSP}	Opcode Register Setup Time	0.31	_	0.35	_	0.39	_	ns
t _{HOPT_DSP}	Opcode Register Hold Time	-0.20	_	-0.24		-0.27	_	ns
t _{SUDATA_DSP}	Cascade_data through ALU to Output Register Setup Time	1.69		1.94		2.14		ns
t _{HPDATA_DSP}	Cascade_data through ALU to Output Register Hold Time	-0.58		-0.80		-0.97		ns

Over Recommended Commercial Operating Conditions

1. Internal parameters are characterized but not tested on every device.

2. Commercial timing numbers are shown. Industrial timing numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

3. DSP slice is configured in Multiply Add/Sub 18 x 18 mode.

4. The output register is in Flip-flop mode.

5. For details on –9 speed grade devices, please contact your Lattice Sales Representative.



SERDES External Reference Clock

The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Symbol	Description	Min.	Тур.	Max.	Units
F _{REF}	Frequency range	15	_	320	MHz
F _{REF-PPM}	Frequency tolerance ¹	-1000	_	1000	ppm
V _{REF-IN-SE}	Input swing, single-ended clock ²	200	_	V _{CCA}	mV, p-p
V _{REF-IN-DIFF}	Input swing, differential clock	200	_	2*V _{CCA}	mV, p-p differential
V _{REF-IN}	Input levels	0	_	V _{CCA} + 0.3	V
D _{REF}	Duty cycle ³	40	_	60	%
T _{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T _{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
Z _{REF-IN-TERM-DIFF}	Differential input termination	-20%	100/2K	+20%	Ohms
C _{REF-IN-CAP}	Input capacitance	_	—	7	pF

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.

2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.

3. Measured at 50% amplitude.

Figure 3-13. SERDES External Reference Clock Waveforms





Serial Rapid I/O Type 2/CPRI LV E.24 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
T _{RF} ¹	Differential rise/fall time	20%-80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance		80	100	120	Ohms
J _{TX_DDJ} ^{3, 4, 5}	Output data deterministic jitter			_	0.17	UI
J _{TX_TJ} ^{2, 3, 4, 5}	Total output data jitter			_	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.

2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.

3. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).

4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	_	_	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—		dB
Z _{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J _{RX_DJ} ^{2, 3, 4, 5}	Deterministic jitter tolerance (peak-to-peak)		_	—	0.37	UI
J _{RX_RJ} ^{2, 3, 4, 5}	Random jitter tolerance (peak-to-peak)		_	—	0.18	UI
J _{RX_SJ} ^{2, 3, 4, 5}	Sinusoidal jitter tolerance (peak-to-peak)		_	—	0.10	UI
J _{RX_TJ} ^{1, 2, 3, 4, 5}	Total jitter tolerance (peak-to-peak)		_	—	0.65	UI
T _{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.

2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.

3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

5. Values are measured at 2.5 Gbps.



Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Te	est Fixture Required	Components,	Non-Terminated Interfaces
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Test Condition	R ₁	R ₂	CL	Timing Ref.	V _T
				LVCMOS 3.3 = 1.5V	
				LVCMOS 2.5 = $V_{CCIO}/2$	
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0 pF	LVCMOS 1.8 = V _{CCIO} /2	
				LVCMOS 1.5 = $V_{CCIO}/2$	_
				LVCMOS 1.2 = V _{CCIO} /2	_
LVCMOS 2.5 I/O (Z -> H)	8	1MΩ	0 pF	V _{CCIO} /2	
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	∞	0 pF	V _{CCIO} /2	V _{CCIO}
LVCMOS 2.5 I/O (H -> Z)	8	100	0 pF	V _{OH} - 0.10	
LVCMOS 2.5 I/O (L -> Z)	100	x	0 pF	V _{OL} + 0.10	V _{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.



PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges	of the Device	
D[Edgo] [n 2]	А	DQ
	В	DQ
P[Edge] [n-2]	A	DQ
	В	DQ
D[Edgo] [n 1]	A	DQ
	В	DQ
P[Edge] [n]	A	[Edge]DQSn
	В	DQ
P[Edge] [n 1]	А	DQ
	В	DQ
D[Edgo] [n 2]	A	DQ
r[Euge][II+2]	В	DQ
For Top Edge of the Devi	ce	
P[Edge] [n-3]	А	DQ
	В	DQ
P[Edge] [n-2]	А	DQ
	В	DQ
P[Edge] [n-1]	А	DQ
	В	DQ
P[Edge] [n]	A	[Edge]DQSn
, [raâc] [ii]	В	DQ
P[Edge] [n+1]	А	DQ
i [Euge] [iit i]	В	DQ
P[Edge] [n 2]	А	DQ
י נבטשכן נוידבן	В	DQ

Note: "n" is a row PIC number.



Pin Information Summary (Cont.)

Pin Information Sun		ECP3-17EA		ECP3-35EA			
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA
	Bank 0	13	10	18	13	21	24
	Bank 1	7	5	12	7	18	18
	Bank 2	2	2	4	1	8	8
Emulated Differential I/O per	Bank 3	4	2	13	5	20	19
Dank	Bank 6	5	1	13	6	22	20
	Bank 7	6	9	10	6	11	13
	Bank 8	12	12	12	12	12	12
	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	2	2	3	3	6	6
Highspeed Differential I/O per	Bank 3	5	4	9	4	9	12
Barik	Bank 6	5	4	9	4	11	12
	Bank 7	5	6	8	5	9	10
	Bank 8	0	0	0	0	0	0
	Bank 0	26/13	20/10	36/18	26/13	42/21	48/24
	Bank 1	14/7	10/5	24/12	14/7	36/18	36/18
	Bank 2	8/4	9/4	14/7	8/4	28/14	28/14
Differential I/O per Bank	Bank 3	18/9	12/6	44/22	18/9	58/29	63/31
	Bank 6	20/10	11/5	44/22	20/10	67/33	65/32
	Bank 7	23/11	30/15	36/18	23/11	40/20	46/23
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
	Bank 0	2	1	3	2	3	4
	Bank 1	1	0	2	1	3	3
	Bank 2	0	0	1	0	2	2
DDR Groups Bonded per Bank ²	Bank 3	1	0	3	1	3	4
	Bank 6	1	0	3	1	4	4
	Bank 7	1	2	2	1	3	3
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	1	1	1	1	1

These pins must remain floating on the board.
 Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.



Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6LFN672C	1.2 V	-6	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7LFN672C	1.2 V	-7	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8LFN672C	1.2 V	-8	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-6LFN1156C	1.2 V	-6	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7LFN1156C	1.2 V	-7	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8LFN1156C	1.2 V	-8	LOW	Lead-Free fpBGA	1156	COM	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672CTW ¹	1.2 V	-6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672CTW ¹	1.2 V	-7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672CTW ¹	1.2 V	-8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156CTW1	1.2 V	-6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156CTW ¹	1.2 V	-7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156CTW1	1.2 V	-8	STD	Lead-Free fpBGA	1156	COM	149

1. Note: Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.

• The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.

• The SERDES XRES pin on the TW device passes CDM testing at 250 V.



Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-70EA-6FN484I	1.2 V	-6	STD	Lead-Free fpBGA	484	IND	67
LFE3-70EA-7FN484I	1.2 V	-7	STD	Lead-Free fpBGA	484	IND	67
LFE3-70EA-8FN484I	1.2 V	-8	STD	Lead-Free fpBGA	484	IND	67
LFE3-70EA-6LFN484I	1.2 V	-6	LOW	Lead-Free fpBGA	484	IND	67
LFE3-70EA-7LFN484I	1.2 V	-7	LOW	Lead-Free fpBGA	484	IND	67
LFE3-70EA-8LFN484I	1.2 V	-8	LOW	Lead-Free fpBGA	484	IND	67
LFE3-70EA-6FN672I	1.2 V	-6	STD	Lead-Free fpBGA	672	IND	67
LFE3-70EA-7FN672I	1.2 V	-7	STD	Lead-Free fpBGA	672	IND	67
LFE3-70EA-8FN672I	1.2 V	-8	STD	Lead-Free fpBGA	672	IND	67
LFE3-70EA-6LFN672I	1.2 V	-6	LOW	Lead-Free fpBGA	672	IND	67
LFE3-70EA-7LFN672I	1.2 V	-7	LOW	Lead-Free fpBGA	672	IND	67
LFE3-70EA-8LFN672I	1.2 V	-8	LOW	Lead-Free fpBGA	672	IND	67
LFE3-70EA-6FN1156I	1.2 V	-6	STD	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-7FN1156I	1.2 V	-7	STD	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-8FN1156I	1.2 V	-8	STD	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-6LFN1156I	1.2 V	-6	LOW	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-7LFN1156I	1.2 V	-7	LOW	Lead-Free fpBGA	1156	IND	67
LFE3-70EA-8LFN1156I	1.2 V	-8	LOW	Lead-Free fpBGA	1156	IND	67

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade ¹	Power	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484I	1.2 V	-6	STD	Lead-Free fpBGA	484	IND	92
LFE3-95EA-7FN484I	1.2 V	-7	STD	Lead-Free fpBGA	484	IND	92
LFE3-95EA-8FN484I	1.2 V	-8	STD	Lead-Free fpBGA	484	IND	92
LFE3-95EA-6LFN484I	1.2 V	-6	LOW	Lead-Free fpBGA	484	IND	92
LFE3-95EA-7LFN484I	1.2 V	-7	LOW	Lead-Free fpBGA	484	IND	92
LFE3-95EA-8LFN484I	1.2 V	-8	LOW	Lead-Free fpBGA	484	IND	92
LFE3-95EA-6FN672I	1.2 V	-6	STD	Lead-Free fpBGA	672	IND	92
LFE3-95EA-7FN672I	1.2 V	-7	STD	Lead-Free fpBGA	672	IND	92
LFE3-95EA-8FN672I	1.2 V	-8	STD	Lead-Free fpBGA	672	IND	92
LFE3-95EA-6LFN672I	1.2 V	-6	LOW	Lead-Free fpBGA	672	IND	92
LFE3-95EA-7LFN672I	1.2 V	-7	LOW	Lead-Free fpBGA	672	IND	92
LFE3-95EA-8LFN672I	1.2 V	-8	LOW	Lead-Free fpBGA	672	IND	92
LFE3-95EA-6FN1156I	1.2 V	-6	STD	Lead-Free fpBGA	1156	IND	92
LFE3-95EA-7FN1156I	1.2 V	-7	STD	Lead-Free fpBGA	1156	IND	92
LFE3-95EA-8FN1156I	1.2 V	-8	STD	Lead-Free fpBGA	1156	IND	92
LFE3-95EA-6LFN1156I	1.2 V	-6	LOW	Lead-Free fpBGA	1156	IND	92
LFE3-95EA-7LFN1156I	1.2 V	-7	LOW	Lead-Free fpBGA	1156	IND	92
LFE3-95EA-8LFN1156I	1.2 V	-8	LOW	Lead-Free fpBGA	1156	IND	92

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.



Date	Version	Section	Change Summary
September 2009	01.4	Architecture	Corrected link in sysMEM Memory Block section.
			Updated information for On-Chip Programmable Termination and modi- fied corresponding figure.
			Added footnote 2 to On-Chip Programmable Termination Options for Input Modes table.
			Corrected Per Quadrant Primary Clock Selection figure.
		DC and Switching Characteristics	Modified -8 Timing data for 1024x18 True-Dual Port RAM (Read-Before- Write, EBR Output Registers)
			Added ESD Performance table.
			LatticeECP3 External Switching Characteristics table - updated data for $t_{\text{DIBGDDR}},t_{\text{W}_\text{PRI}},t_{\text{W}_\text{EDGE}}$ and $t_{\text{SKEW}_\text{EDGE}_\text{DQS}}.$
			LatticeECP3 Internal Switching Characteristics table - updated data for $t_{\mbox{COO_PIO}}$ and added footnote #4.
			sysCLOCK PLL Timing table - updated data for f _{OUT} .
			External Reference Clock Specification (refclkp/refclkn) table - updated data for $V_{REF\text{-IN-SE}}$ and $V_{REF\text{-IN-DIFF}}$
			LatticeECP3 sysCONFIG Port Timing Specifications table - updated data for $\ensuremath{t_{\text{MWC}}}$.
			Added TRLVDS DC Specification table and diagram.
			Updated Mini LVDS table.
August 2009	01.3	DC and Switching Characteristics	Corrected truncated numbers for V_{CCIB} and V_{CCOB} in Recommended Operating Conditions table.
July 2009	01.2	Multiple	Changed references of "multi-boot" to "dual-boot" throughout the data sheet.
	Architectu	Architecture	Updated On-Chip Programmable Termination bullets.
			Updated On-Chip Termination Options for Input Modes table.
			Updated On-Chip Termination figure.
		DC and Switching Characteristics	Changed min/max data for FREF_PPM and added footnote 4 in SERDES External Reference Clock Specification table.
			Updated SERDES minimum frequency.
		Pinout Information	Corrected MCLK to be I/O and CCLK to be I in Signal Descriptions table
May 2009	01.1	All	Removed references to Parallel burst mode Flash.
		Introduction	Features - Changed 250 Mbps to 230 Mbps in Embedded SERDES bul- leted section and added a footnote to indicate 230 Mbps applies to 8b10b and 10b12b applications.
			Updated data for ECP3-17 in LatticeECP3 Family Selection Guide table.
			Changed embedded memory from 552 to 700 Kbits in LatticeECP3 Family Selection Guide table.
		Architecture	Updated description for CLKFB in General Purpose PLL Diagram.
			Corrected Primary Clock Sources text section.
			Corrected Secondary Clock/Control Sources text section.
			Corrected Secondary Clock Regions table.
			Corrected note below Detailed sysDSP Slice Diagram.
			Corrected Clock, Clock Enable, and Reset Resources text section.
			Corrected ECP3-17 EBR number in Embedded SRAM in the LatticeECP3 Family table.
			Added On-Chip Termination Options for Input Modes table.
			Updated Available SERDES Quads per LatticeECP3 Devices table.